

To all our customers

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Renesas Technology Corp.  
Customer Support Dept.  
April 1, 2003

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Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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# 2SD2122(L)/(S), 2SD2123(L)/(S)

Silicon NPN Epitaxial

## RENESAS

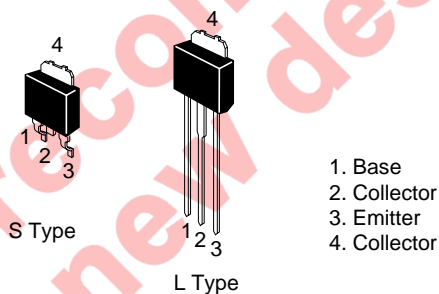
ADE-208-926 (Z)  
1st. Edition  
September 2000

### Application

Low frequency power amplifier complementary pair with 2SB1409(L)/(S)

### Outline

DPAK



## 2SD2122(L)/(S), 2SD2123(L)/(S)

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings		Unit
		2SD2122(L)/(S)	2SD2123(L)/(S)	
Collector to base voltage	$V_{CBO}$	180	180	V
Collector to emitter voltage	$V_{CEO}$	120	160	V
Emitter to base voltage	$V_{EBO}$	5	5	V
Collector current	$I_C$	1.5	1.5	A
Collector peak current	$I_{C(peak)}$	3	3	A
Collector power dissipation	$P_C^{*1}$	18	18	W
Junction temperature	$T_j$	150	150	°C
Storage temperature	$T_{stg}$	-55 to +150	-55 to +150	°C

Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

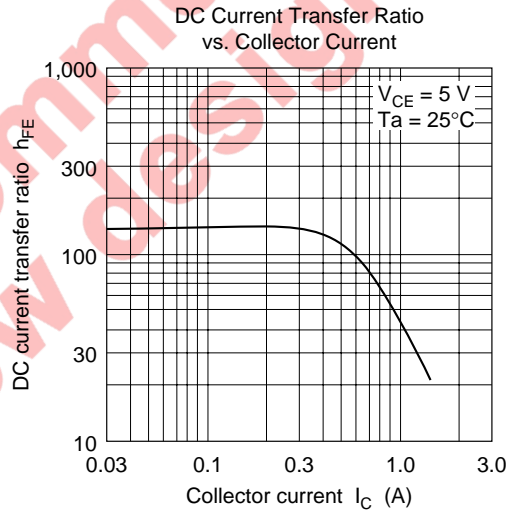
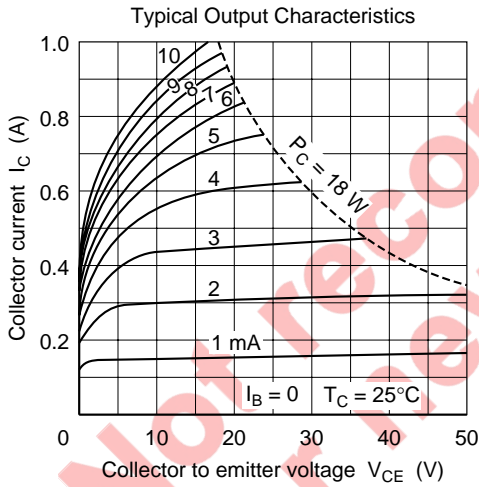
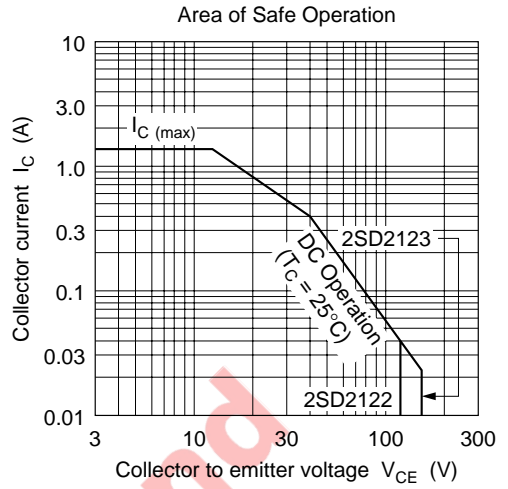
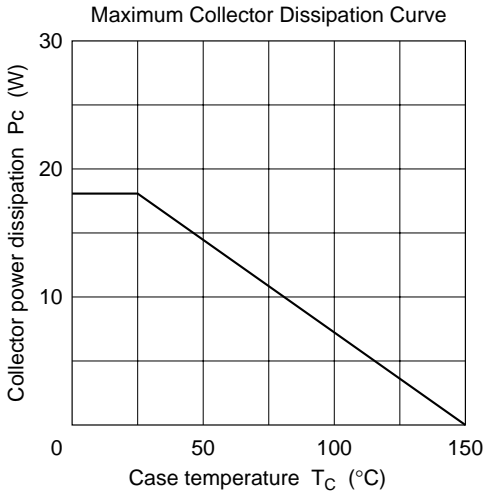
### Electrical Characteristics (Ta = 25°C)

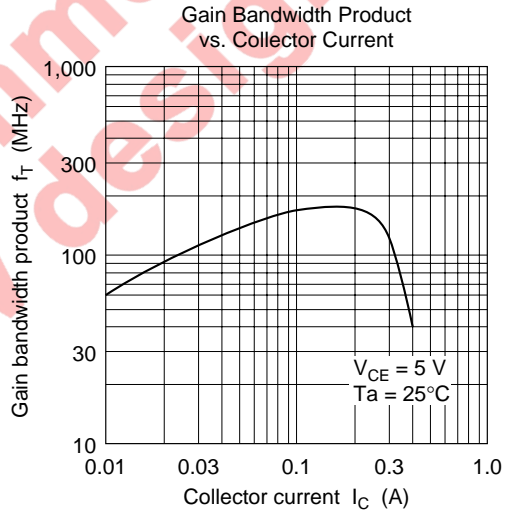
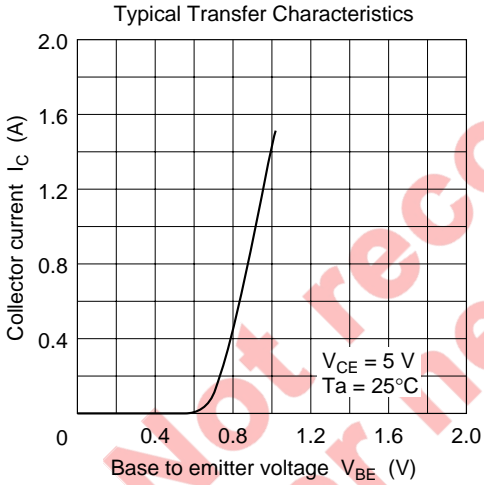
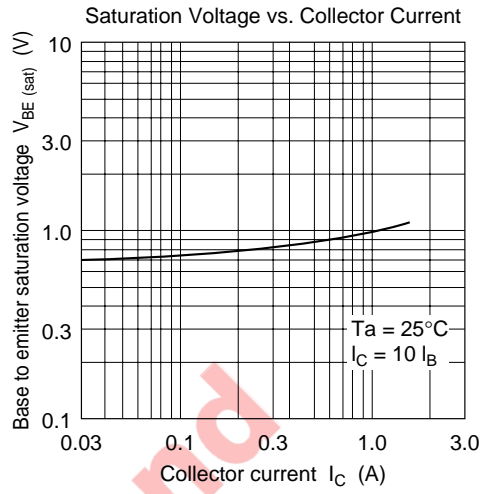
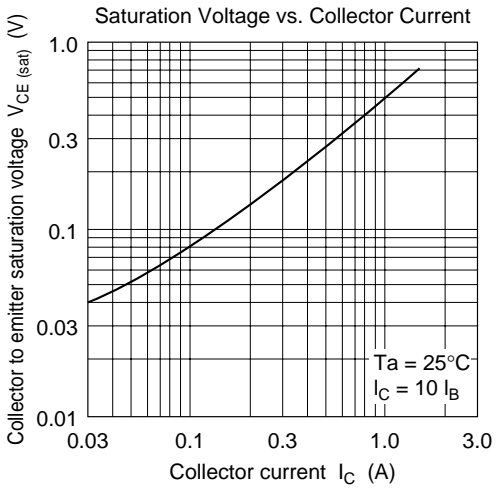
Item	Symbol	2SD2122(L)/(S)			2SD2123(L)/(S)			Unit	Test conditions
		Min	Typ	Max	Min	Typ	Max		
Collector to base breakdown voltage	$V_{(BR)CBO}$	180	—	—	180	—	—	V	$I_C = 1\text{ mA}, I_E = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	120	—	—	160	—	—	V	$I_C = 10\text{ mA}, R_{BE} = \infty$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	5	—	—	V	$I_E = 1\text{ mA}, I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	10	—	—	10	$\mu\text{A}$	$V_{CB} = 160\text{ V}, I_E = 0$
DC current transfer ratio	$h_{FE1}^{*2}$	60	—	200	60	—	200	A	$V_{CE} = 5\text{ V}, I_C = 150\text{ mA}^{*1}$
	$h_{FE2}$	30	—	—	30	—	—		$V_{CE} = 5\text{ V}, I_C = 500\text{ mA}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1	—	—	1	V	$I_C = 500\text{ mA}, I_B = 50\text{ mA}^{*1}$
Base to emitter voltage	$V_{BE}$	—	—	1.5	—	—	1.5	V	$V_{CE} = 5\text{ V}, I_C = 150\text{ mA}^{*1}$
Gain bandwidth product	$f_T$	—	180	—	—	180	—	MHz	$V_{CE} = 5\text{ V}, I_C = 150\text{ mA}^{*1}$
Collector output capacitance	$C_{ob}$	—	14	—	—	14	—	pF	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$

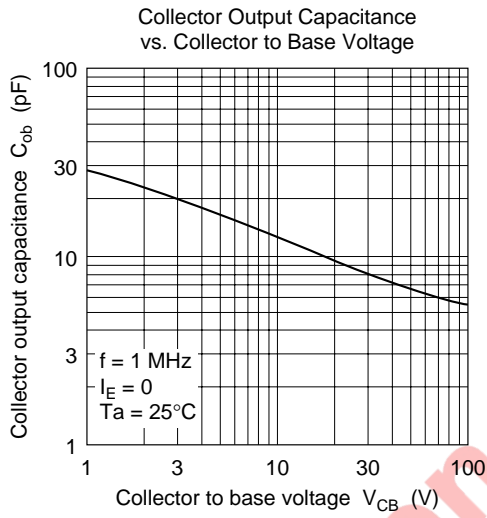
Notes: 1. Pulse test

2. The 2SD2122(L)/(S) and 2SD2123(L)/(S) are grouped by  $h_{FE1}$  as follows.

B	C
60 to 120	100 to 200







Not recommended  
for new design

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